

Current Mirror

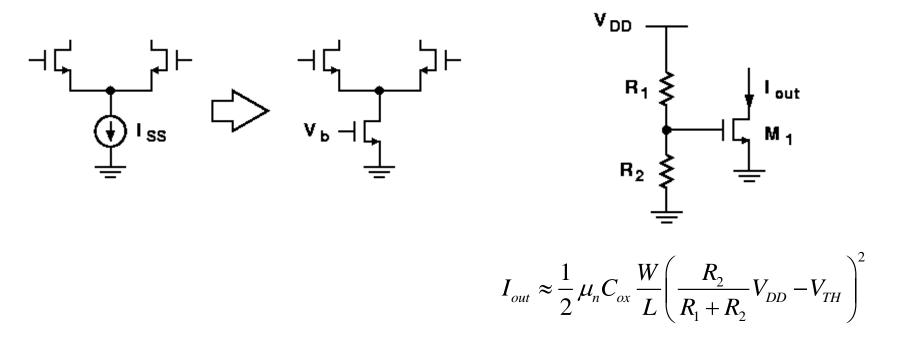
Outline

1. Basic Current Mirrors

- 2. Cascode Current Mirrors
- 3. Active Current Mirrors

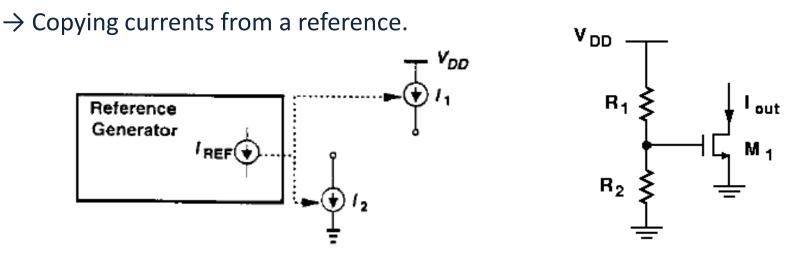
Current Source Issues

- Design issues
 - Voltage headroom.
 - Output impedance.
 - Supply, process, and temperature dependence.
 - Matching.



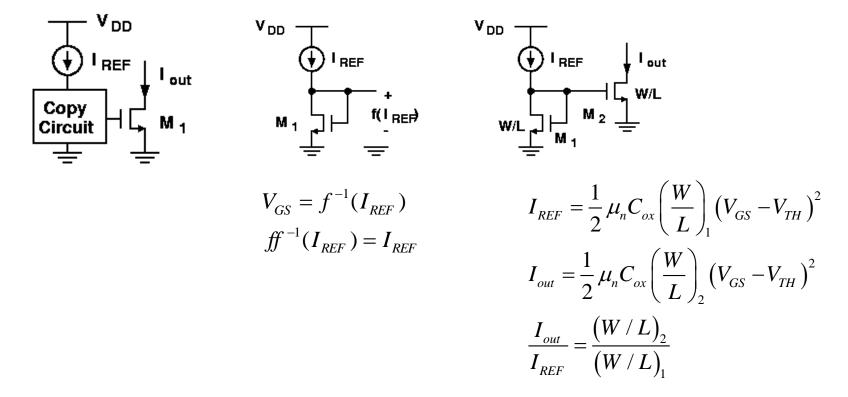
Current Source with Constant V_b

- Depending on supply, process, and temperature.
- The threshold voltage may vary by 100 mV from wafer to wafer.
- Both μ_n and V_{TH} exhibit temperature dependence.
- The issue becomes more severe as the device is biased with a smaller overdrive voltage. (200mV V_{ov} , 50mV ΔV_{TH} cause 44% error)
- If the gate-source voltage of a MOSFET is precisely defined, then its drain current is not.



Basic Current Mirror

• For $I_{out} = I_{REF}$



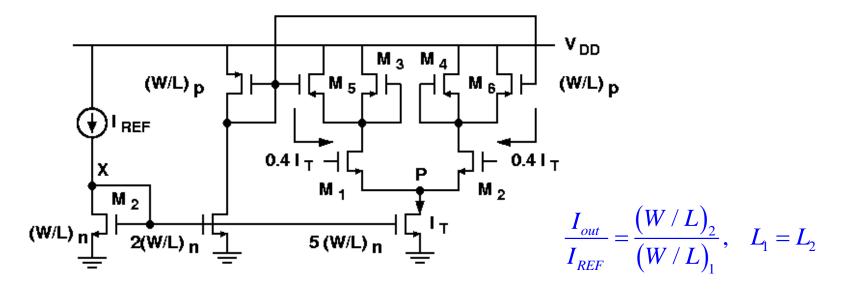
 It allows precise copying of the current with no dependence on process and temperature.

Current Mirror: Sink & Source

 Current mirrors employ the same length for all of the transistors so as to minimize errors due to the side diffusion of the source and drain areas.

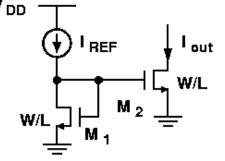
$$L_{eff} = L_{drawn} - 2L_D$$

• Current ratio by only scaling the width of transistors.



Current Mirror with r_o

Channel length modulation effect results in significant error in copying currents.



$$I_{D1} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_1 \left(V_{GS} - V_{TH}\right)^2 \left(1 + \lambda V_{DS1}\right), \quad I_{D2} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_2 \left(V_{GS} - V_{TH}\right)^2 \left(1 + \lambda V_{DS2}\right)$$

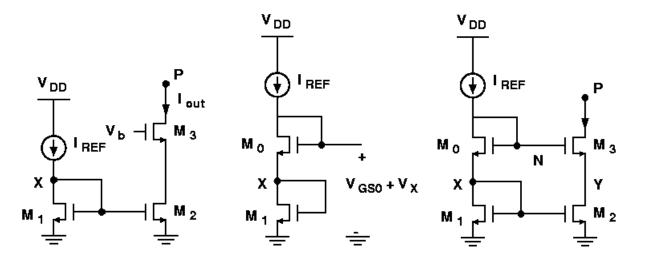
• As
$$\frac{I_{D2}}{I_{D1}} = \frac{(W/L)_2}{(W/L)_1} \frac{1 + \lambda V_{DS2}}{1 + \lambda V_{DS1}}$$
, for $I_{D1} = I_{D2}$, V_{DS1} must be equal to V_{DS2} .

• Use cascode structure to improve the ratio accuracy of current mirror.

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Cascode Current Mirror



• V_b is chosen such that $V_Y = V_X$.

$$V_b - V_{GS3} = V_X$$
, $V_b = V_{GS3} + V_X$, $V_N = V_{GS0} + V_X$
if $\frac{(W/L)_3}{(W/L)_0} = \frac{(W/L)_2}{(W/L)_1}$, then $V_{GS0} = V_{GS3}$ and $V_X = V_Y$

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 Such accuracy is obtained at the cost of the voltage headroom consumed by M₃.

Cascode Current Mirror

• The minimum allowable voltage at node P is equal to

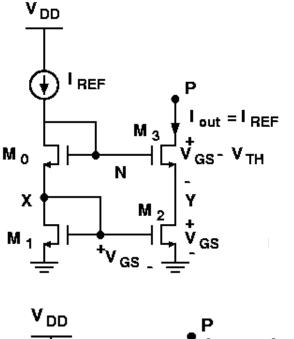
$$\begin{split} V_{N} - V_{TH} &= V_{GS1} + V_{GS0} - V_{TH} \\ &= \left(V_{GS1} - V_{TH} \right) + \left(V_{GS0} - V_{TH} \right) + V_{TH} \end{split}$$

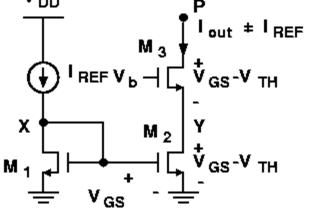
• The voltage of
$$V_N = V_{GS1} + V_{GS0}$$

 For M₂ to be in saturation region, V_b can be chosen as low as

$$V_b = V_{GS3} + V_{DS2}$$

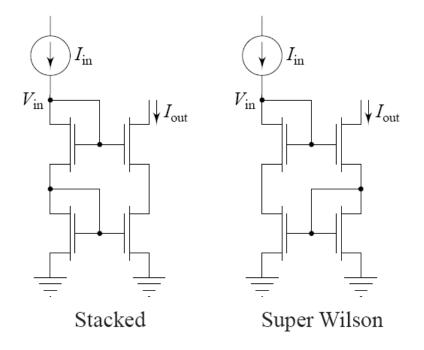
But the output current does not accurately track I_{REF}.





Cascode Current Mirror

- Each of these mirrors is self biasing, has a high output impedance, and provides a low systematic transfer error.
- Each requires an input voltage of two diode drops.
- Each has an output compliance voltage of a diode drop plus a saturation voltage.
- Neither is suitable for use with a low power supply voltage.



Wide-Swing Cascode Current Mirror

- To eliminate the accuracy-headroom trade-off.
- For M2 to be saturated

 $V_b - V_{TH2} \le V_X (= V_{GS1})$

• For M1 to be saturated

 $V_{GS1} - V_{TH1} \le V_A (= V_b - V_{GS2})$

Thus

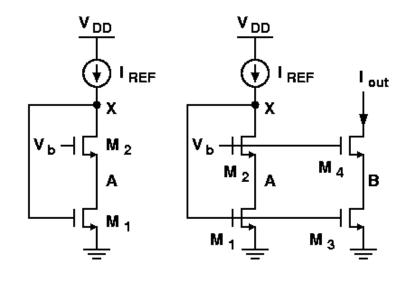
 $V_{GS2} + (V_{GS1} - V_{TH1}) \le V_b \le V_{GS1} + V_{TH2}$

• A solution exist if

$$V_{GS2} + (V_{GS1} - V_{TH1}) \le V_{GS1} + V_{TH2} \Longrightarrow V_{GS2} - V_{TH2} \le V_{TH1}$$

Let

$$V_{GS2} = V_{GS4} \Longrightarrow V_b = V_{GS2} + (V_{GS1} - V_{TH1}) = V_{GS4} + (V_{GS3} - V_{TH3})$$



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Analog IC Analysis and Design

Wide-Swing Cascode Current Mirror

Generation of biased voltage V_h

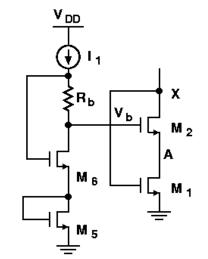
Let
$$V_{GS5} \approx V_{GS2}$$

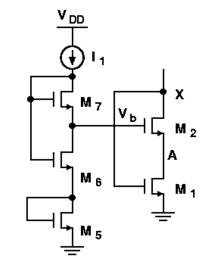
 $V_{DS6} = V_{GS6} - I_1 R_b = V_{DS1}$
 $\Rightarrow If \quad V_{GS6} = V_{GS1}$
 $\Rightarrow I_1 R_b = V_{TH6} = V_{TH1}$

- Some inaccuracy arises because M_5 does not suffer from body effect whereas M₂ does.
- $-I_1R_b$ is not well controlled.
- The diode connected M7 has a large W/L such that

$$\begin{split} V_{GS7} &\approx V_{TH7} \\ V_{DS6} &\approx V_{GS6} - V_{TH7} \\ V_b &= V_{GS5} + V_{GS6} - V_{TH7} \end{split}$$

This circuit suffers from similar errors due to body effect.



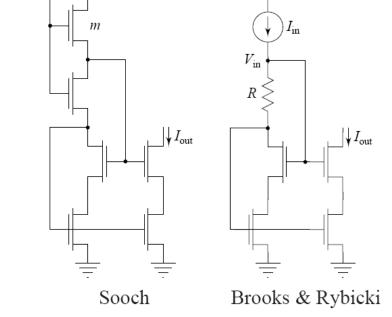


The Sooch mirror requires an input voltage of two diode drops, which

- makes it unsuitable for low-voltage applications.
- The Brooks-Rybicki mirror requires an input voltage of a diode drop plus a saturation voltage, but requires a different value of *R for every I_{in}*.

Wide-Swing Cascode Current Mirror

- All Self biasing, has a high output impedance, and provides a low systematic transfer error.
- Each has an output compliance voltage of two saturation voltages.



 V_{in}

Analog IC Analysis and Design

Wide-Swing Cascode + SF Level Shifter

- Shift the gate voltage of $\rm M_3$ down with respect to $\rm V_N\,$ by interposing a source follower.
- Let M_S 's $V_{GSS} = V_{TH3}$,

$$V_{N'} \approx V_N - V_{TH3}$$

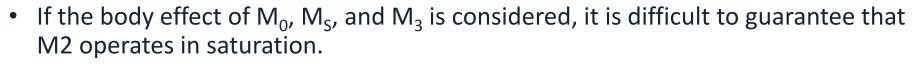
 $V_B = V_{GS1} + V_{GS0} - V_{TH3} - V_{GS3} = V_{GS1} - V_{TH3}$

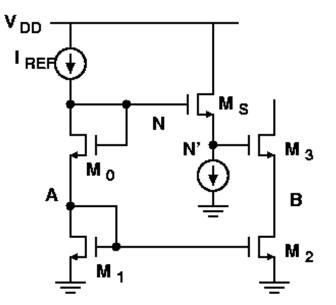
• M_s is biased at a very low current density,

$$V_{GSs} - V_{THs} \approx \sqrt{\frac{2I}{\mu_n C_{ox} W / L}}$$

- M₂ is at the edge of the saturation region.
- Substantial current mismatch is introduced for

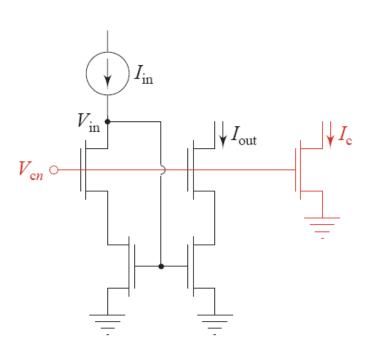
$$V_{DS2} \neq V_{DS1}$$





Wide-Swing Cascode Current Mirror

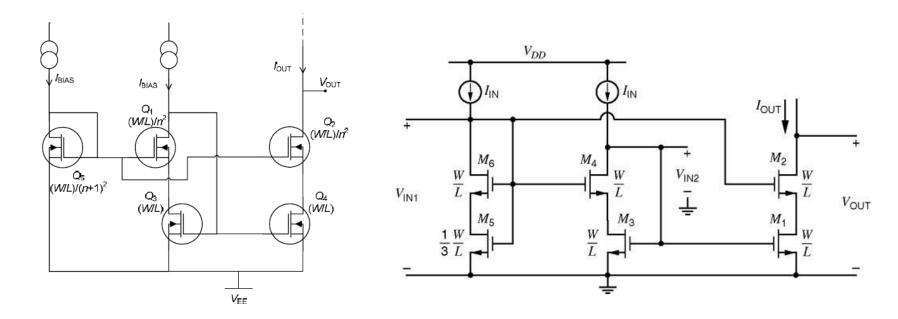
- To facilitate low-voltage operation, we can remove the cascode bias-voltage generation from the input branch.
- The output compliance voltage remains twos saturation voltages.
- The input voltage becomes a diode drop, comparable to that of a simple mirror.
- The optimal value of V_{cn} depends on I_{in}, which sometimes requires us to generate V_{cn} adaptively.



Babanezhad & Gregorian

Wide-Swing Cascode Current Mirror

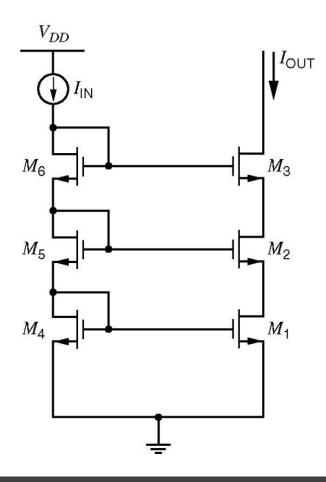
- $V_{OUT} = V_{DS2} + V_{DS4} = V_{OD2} + V_{OD4}$ and $V_{OD4} = nV_{OD2}$
- $V_{OUT min} = V_{OD2} + nV_{OD2} = (n + 1)V_{OD}$, Often n = 1; $V_{OUT min} = 2(V_{GS2} V_t)$



$$V_{IN1} = V_{DS5} + V_{DS6} = V_t + 2V_{OV}$$
$$V_{IN2} = V_{GS3} = V_t + V_{OV}$$

Double-Cascode Current Mirror

- Higher output impedance, more current ratio accuracy
- Smaller output swing



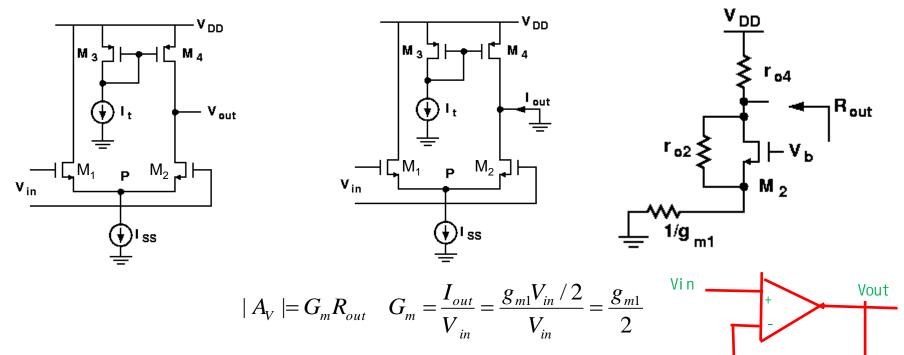
Outline

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- 2. Cascode Current Mirrors
- **3. Active Current Mirrors**

Active Current Mirror

differential in single-ended out amplifier

• Current mirror can also process signals



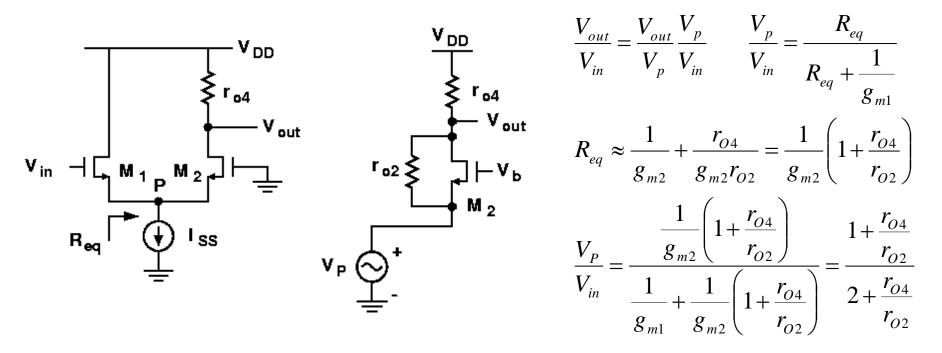
• The output impedance looking into the drain of M₂ is

$$(1 + g_{m2}r_{O2})(1/g_{m1,2}) + r_{O2} = 2r_{O2} + 1/g_{m1} \approx 2r_{O2}$$
$$R_{out} \approx (2r_{O2}) ||r_{O4} \Rightarrow |A_{v}| \approx \frac{g_{m1}}{2} [(2r_{O2})||r_{O4}] \text{ If } r_{O4} \to \infty \Rightarrow |A_{v}| \approx g_{m1}r_{O2}$$

Thus,

Active Current Mirror

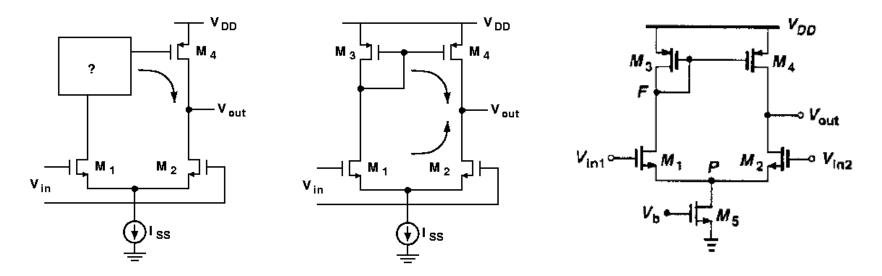
• An Alternative Solution



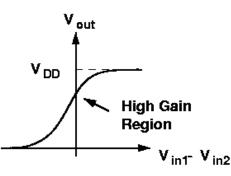
$$\frac{V_{out}}{V_{in}} = \frac{1 + \frac{r_{O4}}{r_{O2}}}{2 + \frac{r_{O4}}{r_{O2}}} \cdot \frac{g_{m2}r_{O2}}{1 + \frac{r_{O2}}{r_{O4}}} = \frac{g_{m2}r_{O2}r_{O4}}{2r_{O2} + r_{O4}} = \frac{g_{m2}}{2} \left[(2r_{O2}) \| r_{O4} \right]$$

Differential to Single-Ended Amplifier

• Current combination utilizing current mirror.



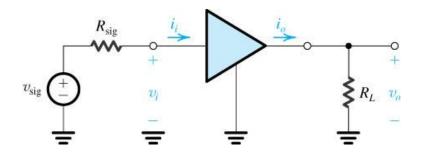
- If V_{in1} is much more negative than V_{in2} , M_1 is off and so are M_3 and M_4 . Both M_2 and M_5 operate in deep triode region.
- For a small $|V_{in1} V_{in2}|$, $M_1 M_4$ are saturated => high gain
- The minimum input voltage level of $V_{in2} = V_{GS1,2} + V_{DS5,min}$
- With perfect symmetry, $V_{out} = V_F = V_{DD} |V_{GS3}|$.
- But V_{out} can vary a lot if device mismatches occur.



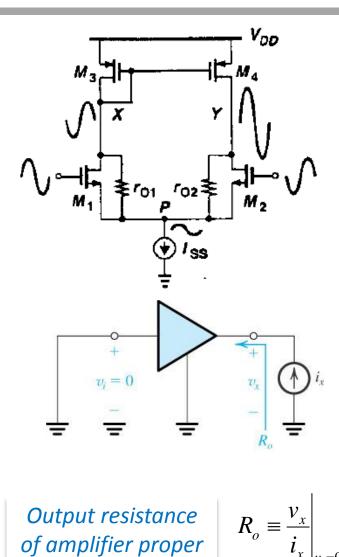
Small-Signal Analysis

 Node "P" is not a virtual ground since amplitude of V_x ≠ V_y

• Find G_m and R_{out} , $|A_v| = G_m R_{out}$,

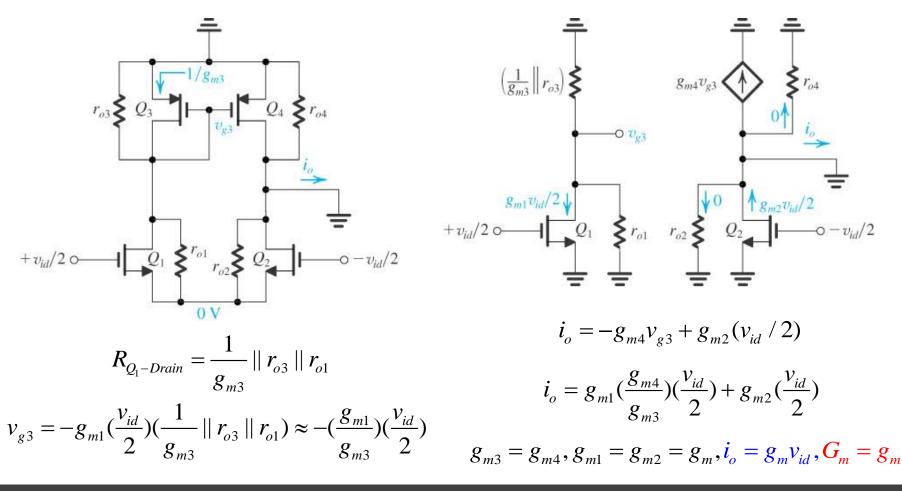


 $\begin{array}{c|c} Short-circuit\\ Transconductance \end{array} & G_m \equiv \frac{i_o}{v_i} \end{array}$



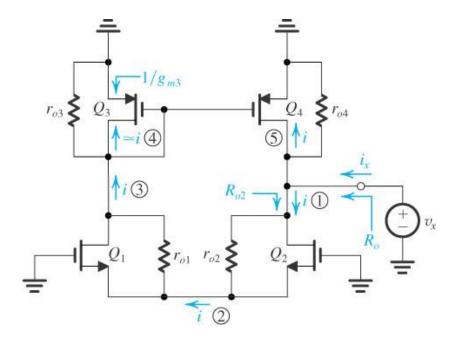
Transconductance G_m

• The impedance from Q1 drain to ground is small, it makes source node as virtual ground.



Analog IC Analysis and Design

Determining the Output Resistance R_o



For
$$g_{m1} = g_{m2} = g_m$$
, $g_{m2}r_{02} >> 1$
 $\Rightarrow R_{o2} \cong 2r_{02}$
 $i_x = \frac{v_x}{R_{o2}} + \frac{v_x}{r_{o4}}$
 $R_o = R_{o2} \parallel r_{o4} \cong \frac{1}{2}r_o$

 $R_{a} = r_{a} + (1 + g_{a} r_{a})(1/g_{a}) \approx 2r_{aa}$

•
$$G_m = g_{m1.2} \cong g_m, R_{out} = R_o \cong \frac{1}{2} r_o$$

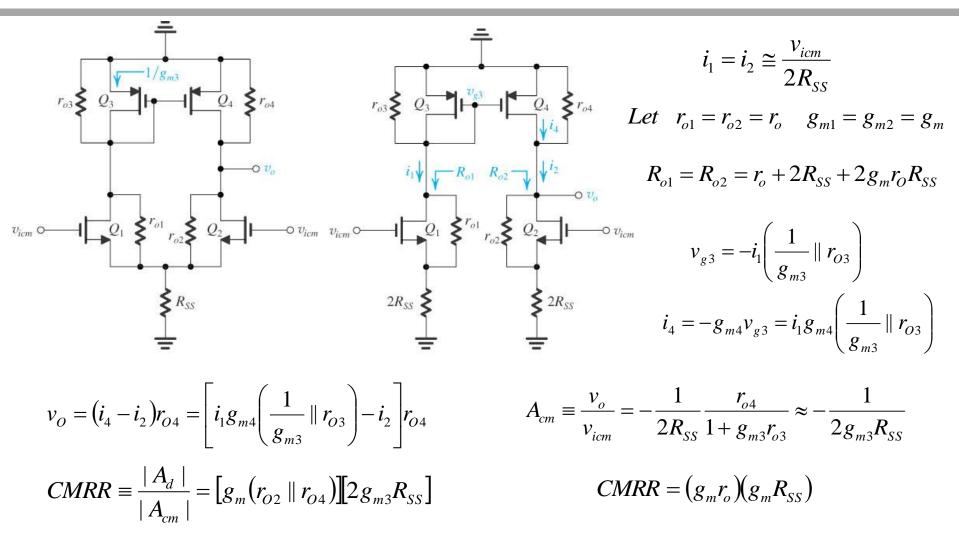
• $|A_v| = G_m R_{out} = g_m [(2r_{O2}) || r_{O4}] \cong \frac{1}{2} g_m r_o$

compared to p.21

$$A_{v} = \frac{g_{m2}}{2} [(2r_{O2}) || r_{O4}],$$
6dB improved

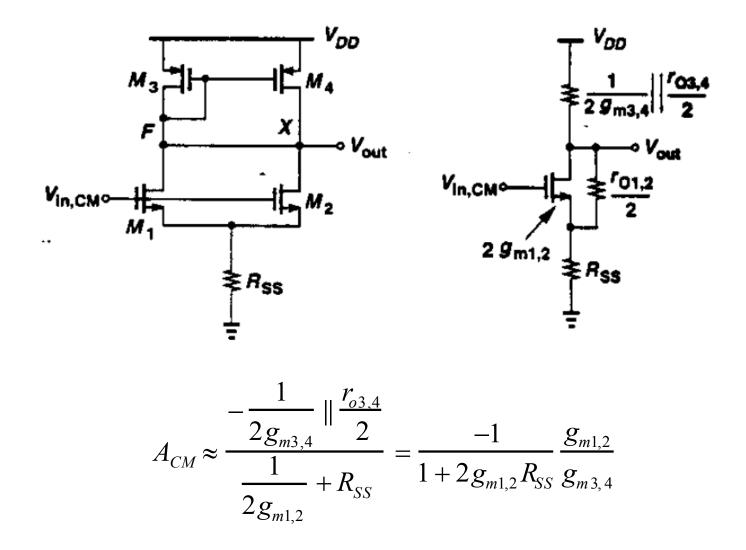
Analog IC Analysis and Design

Common-Mode Gain and CMRR



• The active-loaded MOS differential amplifier has a low A_{cm} and a high CMRR.

Common-Mode Gain Cont.



Analog IC Analysis and Design

Differential Pair with g_m Mismatch

• Voltage change at *P* can be obtained by considering M₁ and M₂ as a single transistor in a SF configuration. $\Delta V_{P} = \Delta V_{in,CM} \frac{K_{SS}}{R_{SS} + \frac{1}{g_{m1} + g_{m2}}}$ P ≩A_{SS} $\Delta I_{D1} = g_{m1} \left(\Delta V_{in,CM} - \Delta V_P \right) = \frac{\Delta V_{in,CM}}{R_{SS} + \frac{1}{g_{m1} + g_{m2}}} \frac{g_{m1}}{g_{m1} + g_{m2}}, \quad \Delta I_{D2} = g_{m2} \left(\Delta V_{in,CM} - \Delta V_P \right) = \frac{\Delta V_{in,CM}}{R_{SS} + \frac{1}{g_{m1} + g_{m2}}} \frac{g_{m2}}{g_{m1} + g_{m2}}$ $\Delta I_{D4} = \Delta I_{D1} \left(\frac{1}{g_{m3}} \parallel r_{O3} \right) g_{m4}, \quad \Delta V_{out} = \left[\Delta I_{D4} - \Delta I_{D2} \right] r_{O4} = \left| \frac{g_{m1} \Delta V_{in,CM}}{1 + (g_{m1} + g_{m2}) R_{SS}} \frac{r_{O3}}{r_{O3} + \dots} - \frac{g_{m2} \Delta V_{in,CM}}{1 + (g_{m1} + g_{m2}) R_{SS}} \right| r_{O4}$ $\Delta V_{out} = \frac{\Delta V_{in,CM}}{1 + (g_{m1} + g_{m2})R_{SS}} \frac{(g_{m1} - g_{m2})r_{O3} - g_{m2} / g_{m3}}{r_{O3} + \dots} r_{O4}, \qquad \frac{\Delta V_{out}}{\Delta V_{in,CM}} \approx \frac{(g_{m1} - g_{m2})r_{O3} - g_{m2} / g_{m3}}{1 + (g_{m1} + g_{m2})R_{SS}}$

Analog IC Analysis and Design